60V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D T_A = +25°C
60V	140mΩ @ V_{GS} = 10V	2.3A
	170mΩ @ V_{GS} = 4.5V	2.1A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMN6140LQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**
  https://www.diodes.com/quality/product-definitions/

Description and Applications

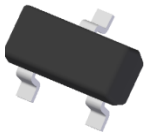
This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- DC-DC converters
- Power-management functions
- Analog switches

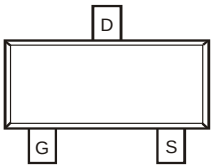
Mechanical Data

- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.0072 grams (Approximate)

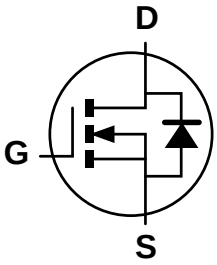
SOT23



Top View



Pin Configuration



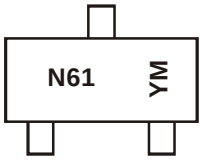
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMN6140LQ-7	SOT23	3,000	Tape & Reel
DMN6140LQ-13	SOT23	10,000	Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



N61 = Product Type Marking Code
YM = Date Code Marking
Y or $\bar{Y}$ = Year (ex: K = 2023)
M = Month (ex: 9 = September)

Date Code Key

Year	2015	-	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032
Code	C	-	K	L	M	N	P	R	S	T	U	V

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 5) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	1.6 1.2	A
	t < 10s	T_A = +25°C T_A = +70°C	I_D	2.0 1.6	A
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	2.3 1.8	A
	t < 10s	T_A = +25°C T_A = +70°C	I_D	2.9 2.3	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	1.5	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	10	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	0.7	W
	T_A = +70°C		0.4	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	183	°C/W
	t < 10s		115	
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	1.3	W
	T_A = +70°C		0.8	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	94	°C/W
	t < 10s		61	
Thermal Resistance, Junction to Case		$R_{\theta JC}$	39	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 60V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	1	—	3	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	92	140	mΩ	V_{GS} = 10V, I_D = 1.8A
			115	170		V_{GS} = 4.5V, I_D = 1.3A
Forward Transfer Admittance	$\|Y_{fs}\|$	—	2.2	—	S	V_{DS} = 15V, I_D = 1.8A
Diode Forward Voltage	V_{SD}	—	0.75	1.0	V	V_{GS} = 0V, I_S = 0.45A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	315	—	pF	V_{DS} = 40V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	18	—		
Reverse Transfer Capacitance	C_{rss}	—	16	—		
Gate Resistance	R_g	—	0.65	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge (V_{GS} = 10V)	Q_g	—	8.6	—	nC	V_{DS} = 30V, I_D = 1.8A
Total Gate Charge (V_{GS} = 5V)	Q_g	—	4.1	—		
Gate-Source Charge	Q_{gs}	—	1.0	—		
Gate-Drain Charge	Q_{gd}	—	1.7	—		
Turn-On Delay Time	$t_{D(ON)}$	—	2.6	—	ns	V_{DS} = 30V, V_{GS} = 10V, R_G = 6.0Ω, I_D = 1.8A
Turn-On Rise Time	t_R	—	3.6	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	16.3	—		
Turn-Off Fall Time	t_F	—	2.7	—		
Reverse Recovery Time	t_{RR}	—	16.8	—	ns	I_F = 1.8A, di/dt =100A/µs
Reverse Recovery Charge	Q_{RR}	—	9.0	—	nC	

Notes:
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1in. square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

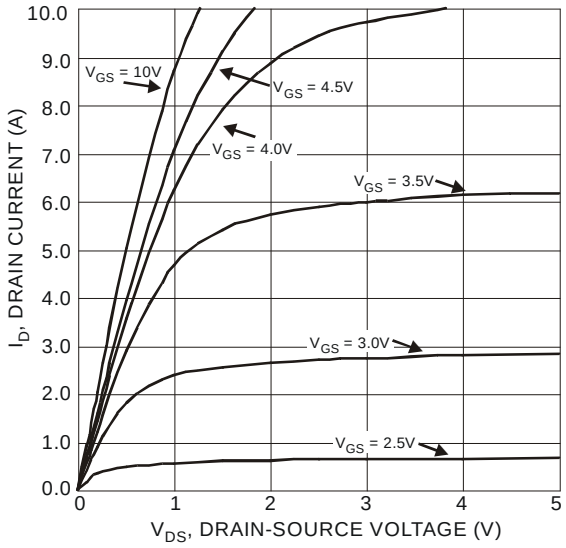


Figure 1 Typical Output Characteristic

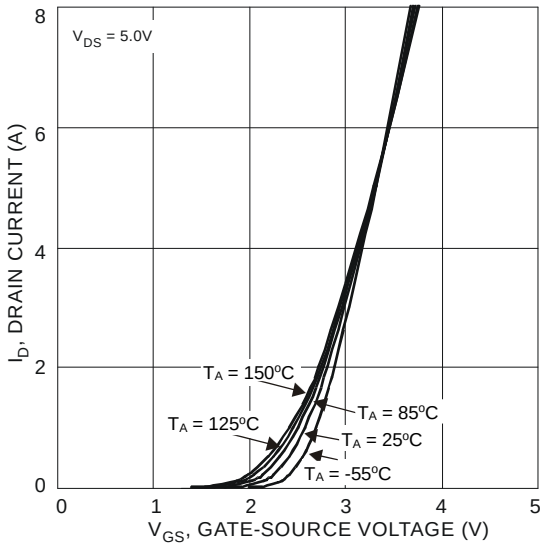


Figure 2 Typical Transfer Characteristics

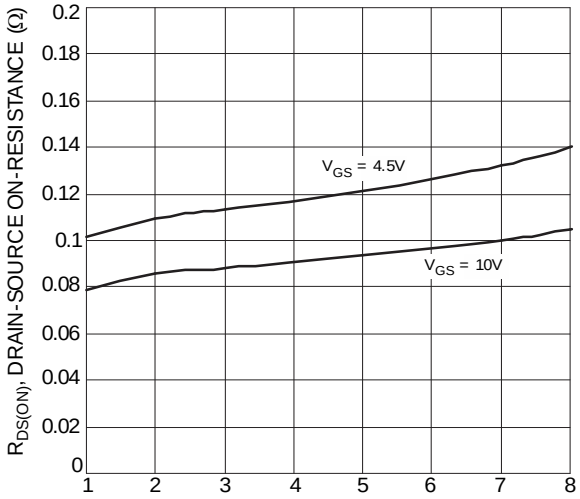


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

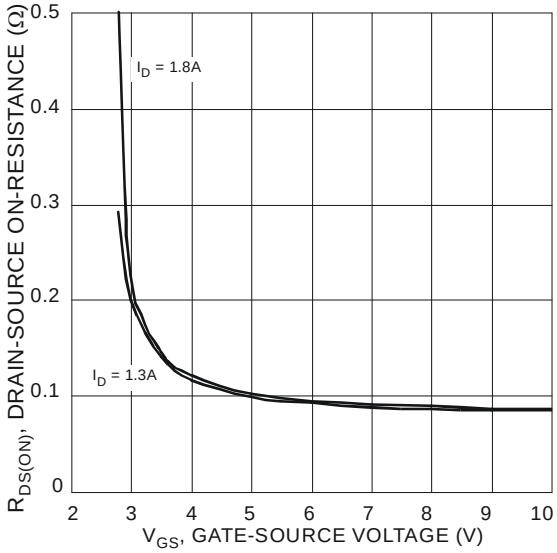


Figure 4 Typical Drain-Source On Resistance vs. Gate-Source Voltage

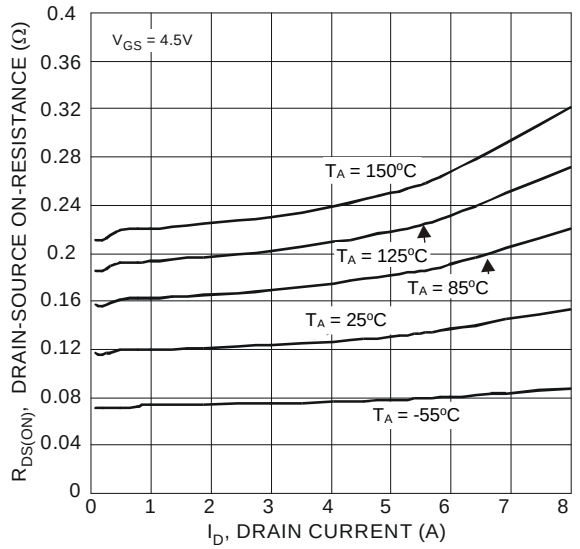


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

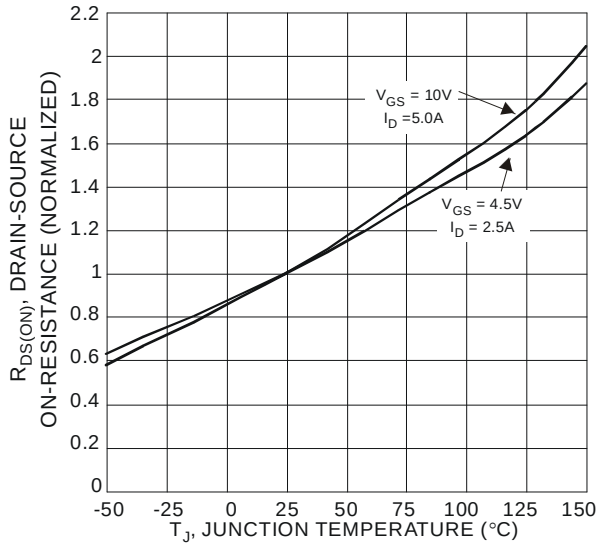


Figure 6 On-Resistance Variation with Temperature

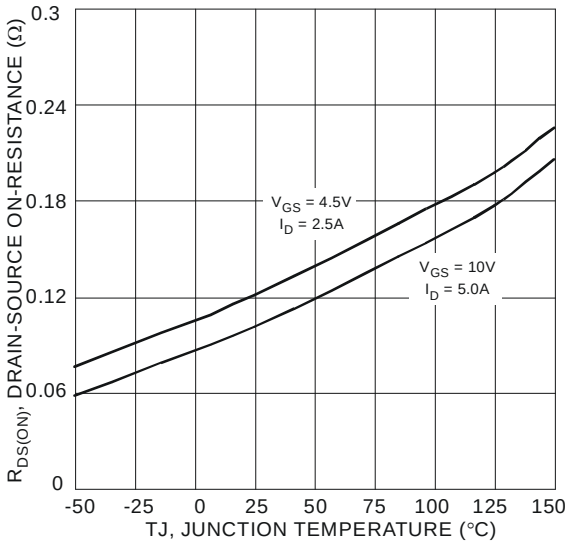


Figure 7 On-Resistance Variation with Temperature

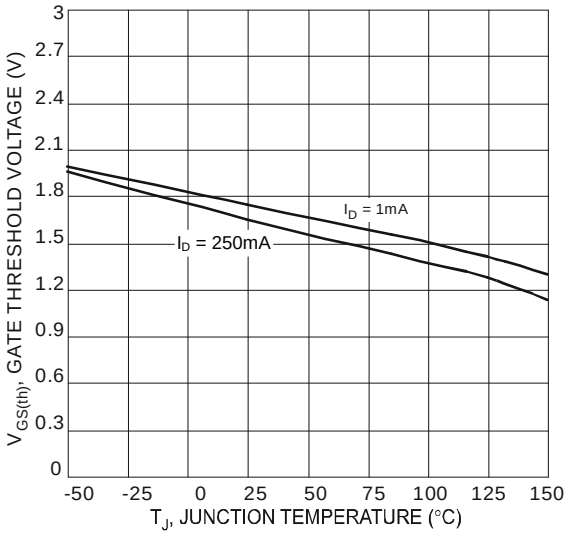


Figure 8 Gate Threshold Variation vs. Ambient Temperature

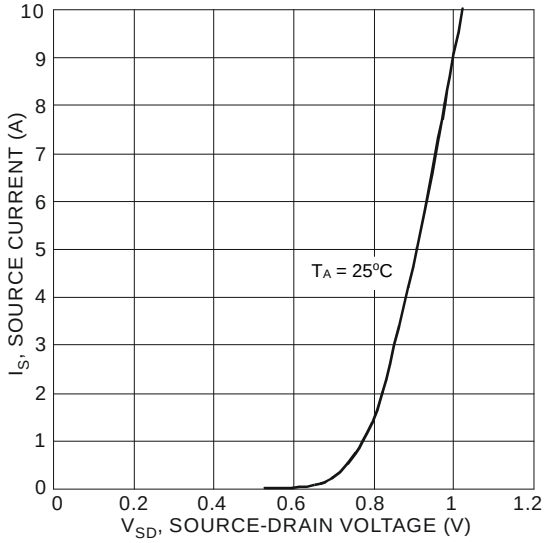


Figure 9 Diode Forward Voltage vs. Current

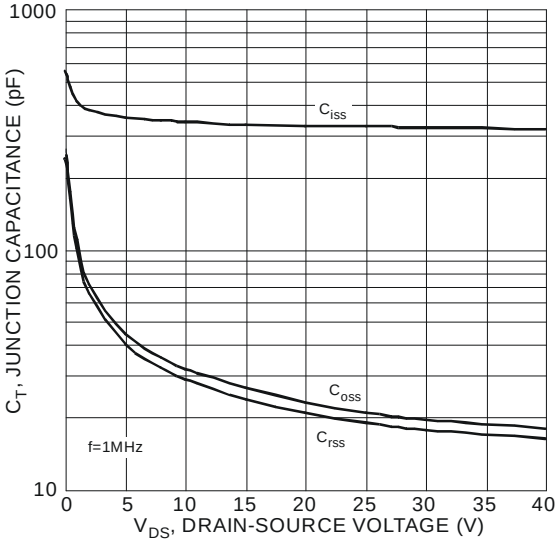


Figure 10 Typical Junction Capacitance

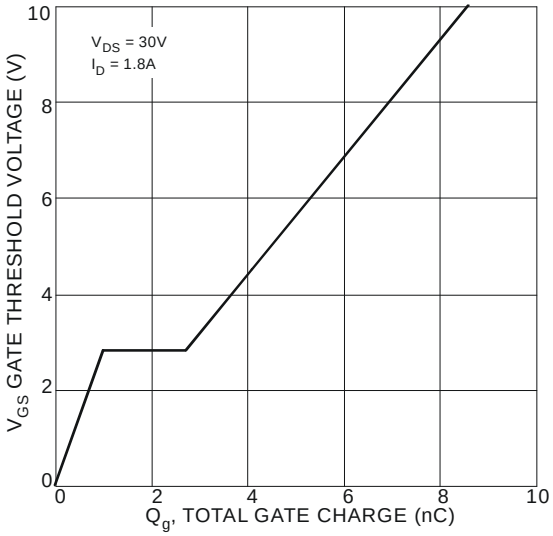


Figure 11 Gate Charge

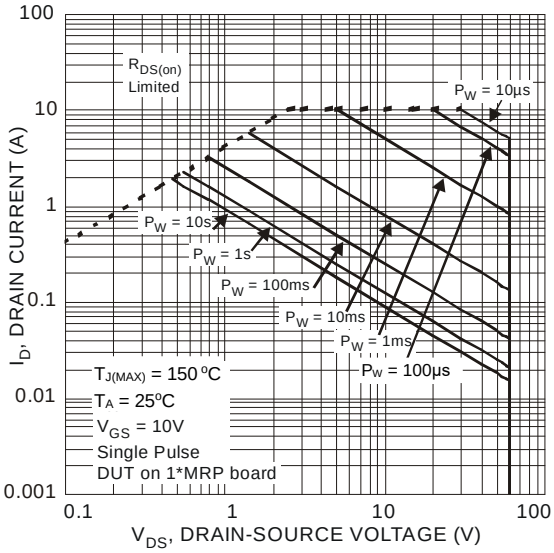


Figure 12 SOA, Safe Operation Area

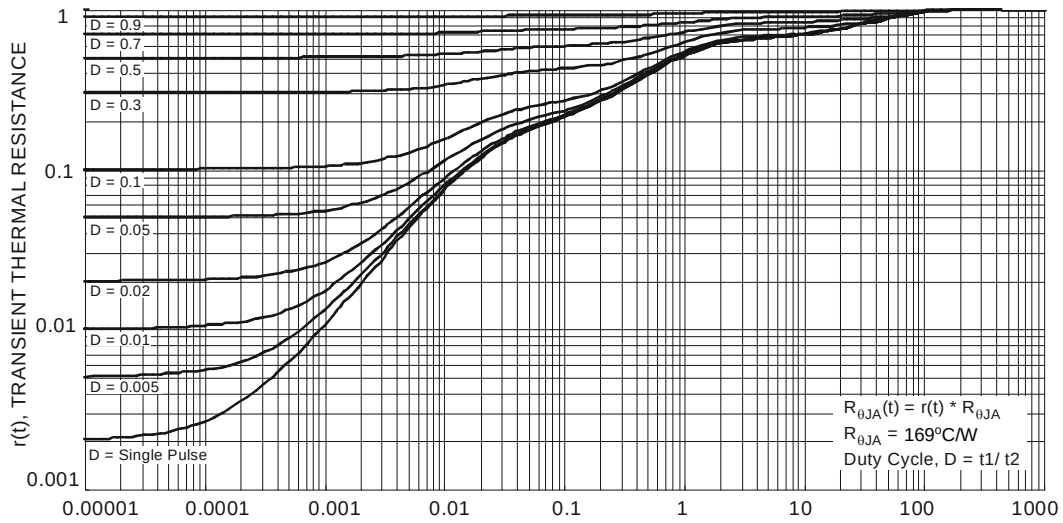
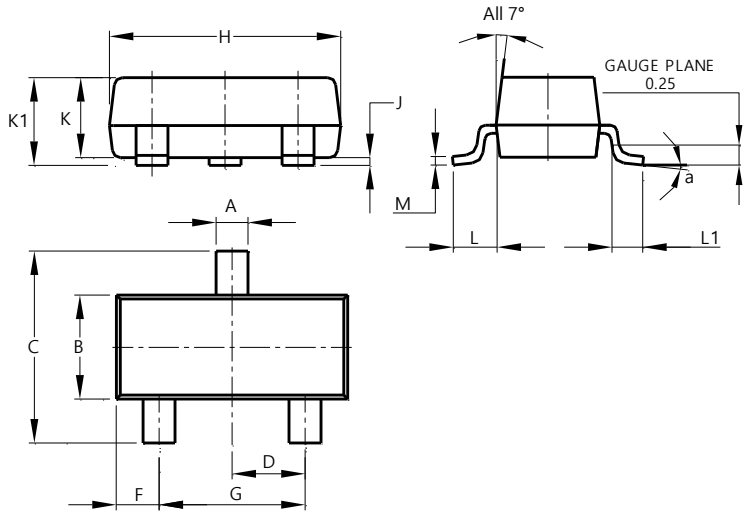


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

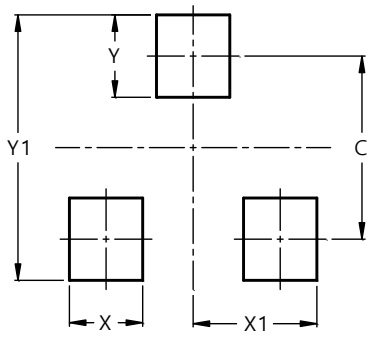


SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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